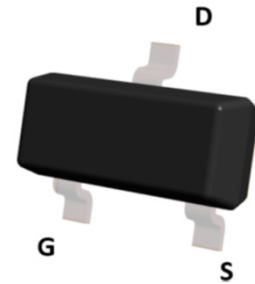
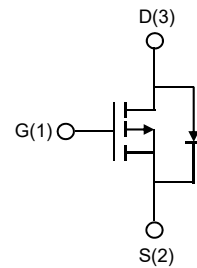
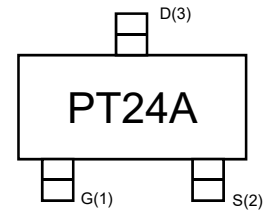


## Description

The MOSFET provide the best combination of fast switching , low on-resistance and cost-effectiveness.

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage


**Top View**

**Circuit Diagram**

**Marking (Top View)**

| MOSFET Product Summary |                       |          |
|------------------------|-----------------------|----------|
| $V_{DS}(V)$            | $R_{DS(on)}(m\Omega)$ | $I_D(A)$ |
| -20                    | 32@ $V_{GS} = -4.5V$  | -4.0     |
|                        | 42@ $V_{GS} = -2.5V$  |          |

## Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

## Absolute maximum rating@25°C

| Rating                                 |                   | Symbol         | Value    | Units |
|--|-------------------|----------------|----------|-------|
| Drain-source Voltage                   |                   | $V_{DS}$       | -20      | V     |
| Gate-source Voltage                    |                   | $V_{GS}$       | $\pm 12$ | V     |
| Drain Current                          |                   | $I_D$          | -4.0     | A     |
| Pulsed Drain Current                   |                   | $I_{DM}$       | -35      | A     |
| Total Power Dissipation                | $T_A=25^\circ C$  | $P_D$          | 0.83     | W     |
|  | $T_A=125^\circ C$ |                | 0.17     |       |
| Junction and Storage Temperature Range |                   | $T_J, T_{STG}$ | -55~+150 | °C    |

## Electrical characteristics per line@25°C (unless otherwise specified)

| Parameter                         | Symbol       | Conditions  | Min. | Typ. | Max.      | Units      |
|-----------------------------------|--------------|---|------|------|-----------|------------|
| <b>OFF Characteristics</b>        |              |   |      |      |           |            |
| Drain-Source Breakdown Voltage    | $BV_{DSS}$   | $V_{GS} = 0V, I_D = -250\mu A$                                    | -20  | -    | -         | V          |
| Zero Gate Voltage Drain Current   | $I_{DSS}$    | $V_{DS} = -20V, V_{GS} = 0V$                                      | -    | -    | -1        | $\mu A$    |
| Gate-Body Leakage Current         | $I_{GSS}$    | $V_{GS} = \pm 12V, V_{DS} = 0V$                                   | -    | -    | $\pm 100$ | nA         |
| Gate Threshold Voltage            | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\mu A$                                | -0.4 | -    | -1.0      | V          |
| Static Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS} = -4.5V, I_D = -5.0A$                                     | -    | 32   | 45        | m $\Omega$ |
|                                   |              | $V_{GS} = -2.5V, I_D = -3.0A$                                     | -    | 42   | 60        |            |
| <b>Dynamic Parameters</b>         |              |   |      |      |           |            |
| Input Capacitance                 | $C_{iss}$    | $V_{DS} = -10V, V_{GS} = 0V,$<br>$f = 1MHz$                       | -    | 859  | -         | pF         |
| Output Capacitance                | $C_{oss}$    |   | -    | 122  | -         |            |
| Reverse Transfer Capacitance      | $C_{rss}$    |   | -    | 106  | -         |            |
| <b>Switching Parameters</b>       |              |   |      |      |           |            |
| Turn-on Delay Time                | $t_{D(on)}$  | $V_{Gen} = -4.5V, V_{DD} = -10V,$<br>$R_G = 1\Omega, I_D = -3.3A$ | -    | 6.0  | -         | ns         |
| Turn-on Rise Time                 | $t_r$        |   | -    | 22.5 | -         |            |
| Turn-off Delay Time               | $t_{D(off)}$ |   | -    | 29   | -         |            |
| Turn-off Fall Time                | $t_f$        |   | -    | 35   | -         |            |

Typical Characteristics

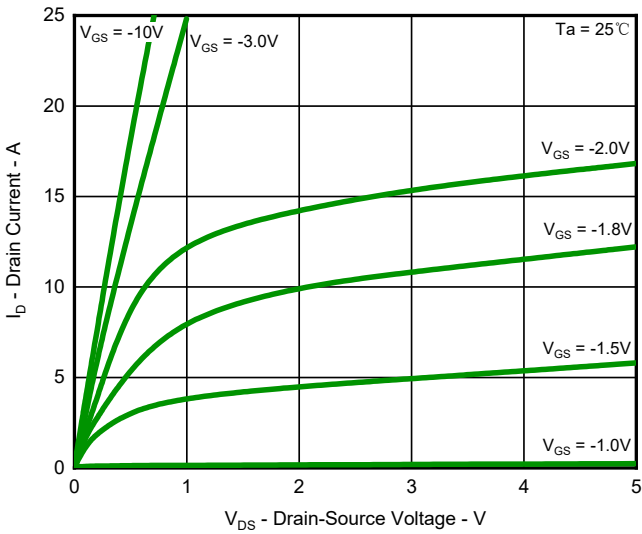


Fig.1 Output Characteristics

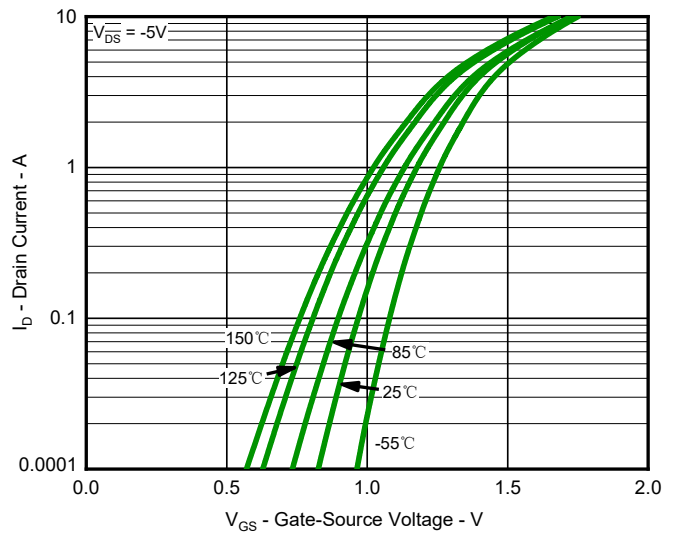


Fig.2 Typical Transfer Characteristic

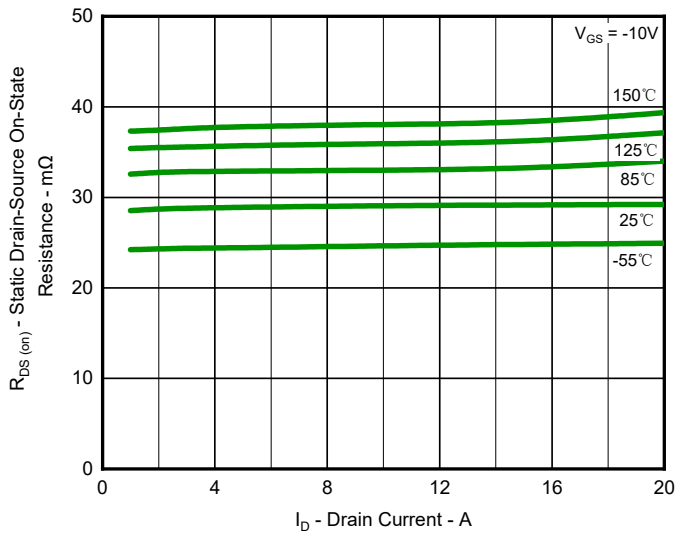


Fig.3 Typical On-Resistance vs Drain Current and Temperature

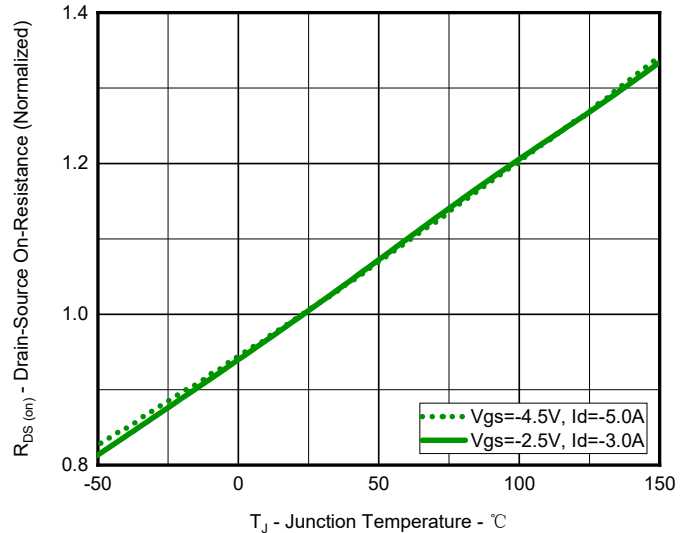


Fig.4 On-Resistance Variation with Temperature(I)

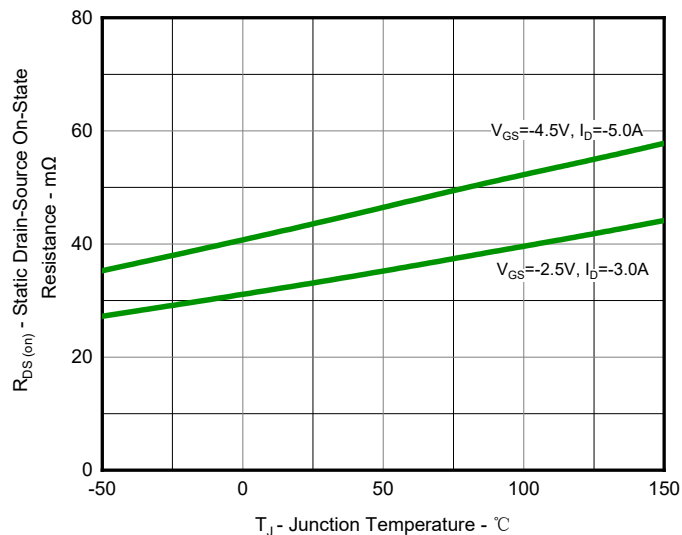


Fig.5 On-Resistance Variation with Temperature(II)

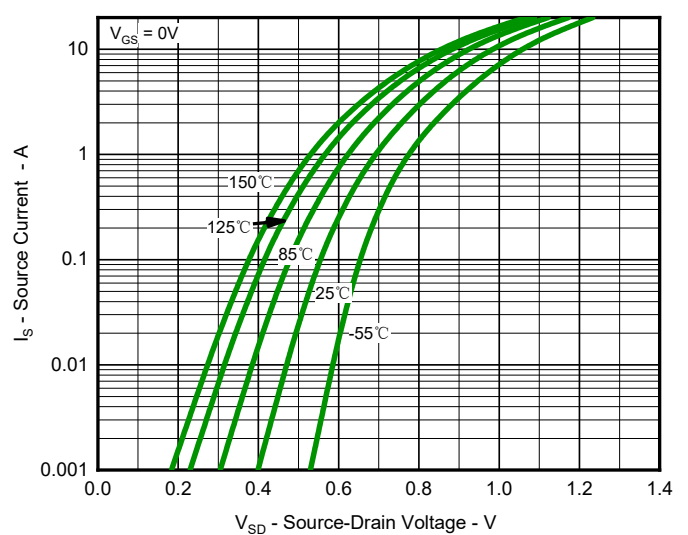
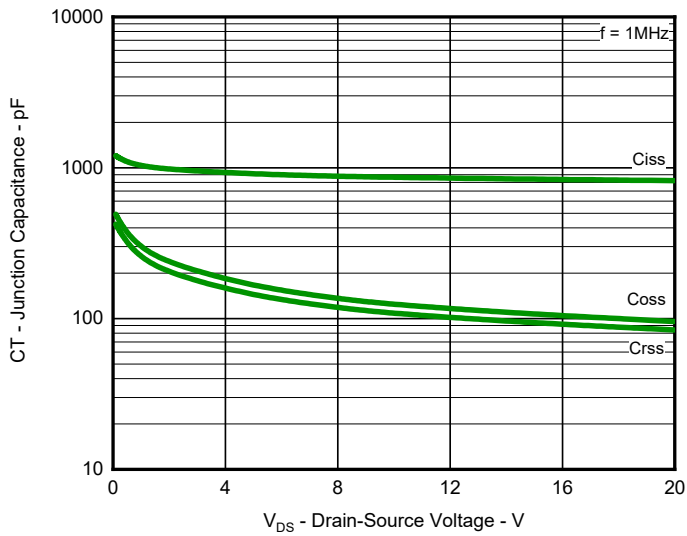
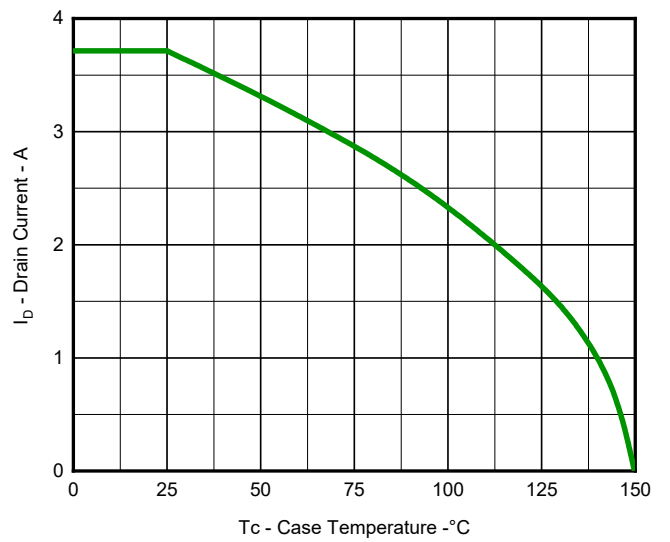


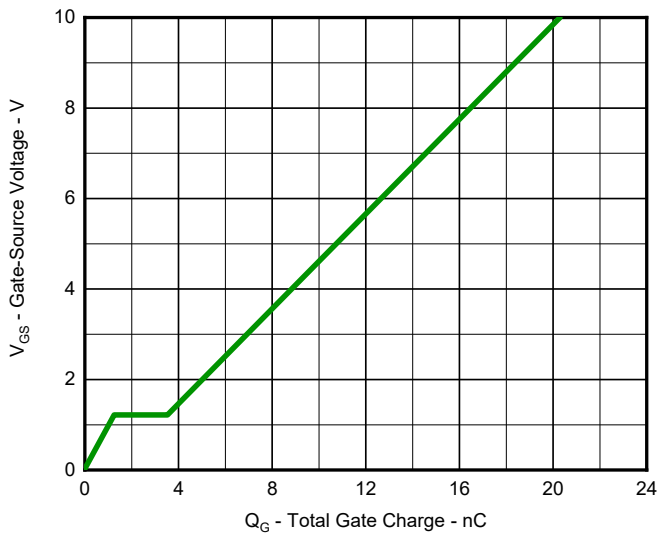
Fig.6 Diode Forward Voltage vs. Current



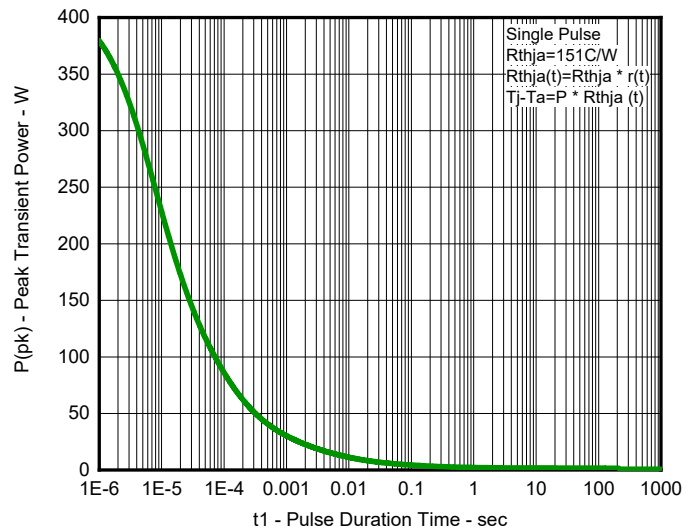
**Fig.7 Typical Junction Capacitance**



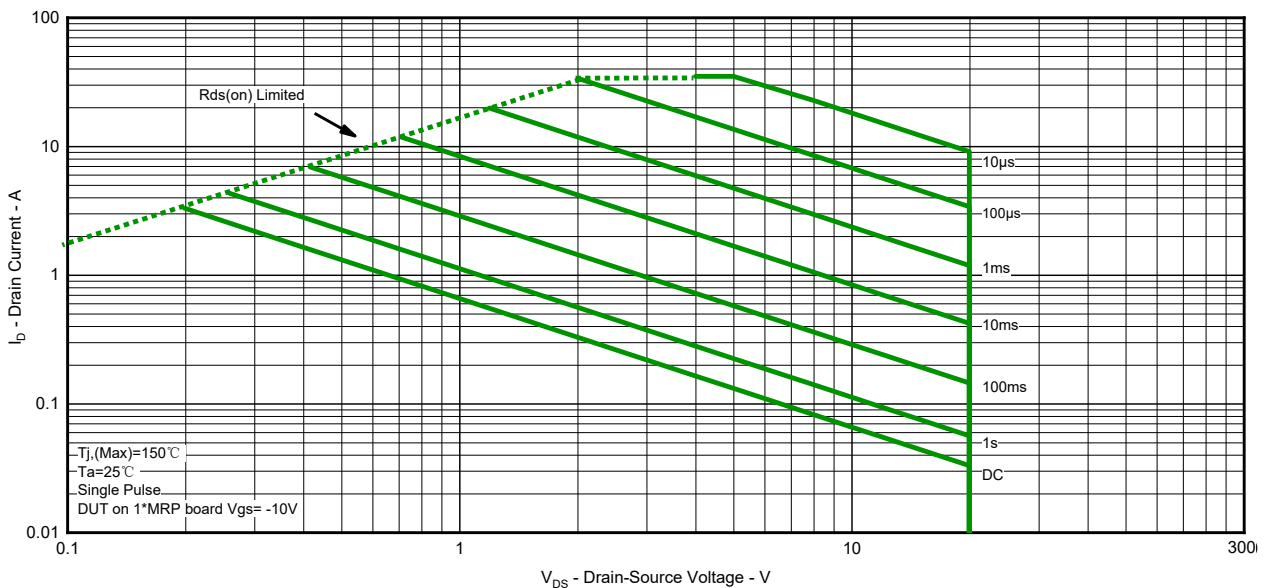
**Fig.8 Maximum Drain Current vs. Case Temperature**



**Fig.9 Gate Charge Characteristics**



**Fig.10 Single Pulse Maximum Power Dissipation**



**Fig.11 Safe Operation Area**

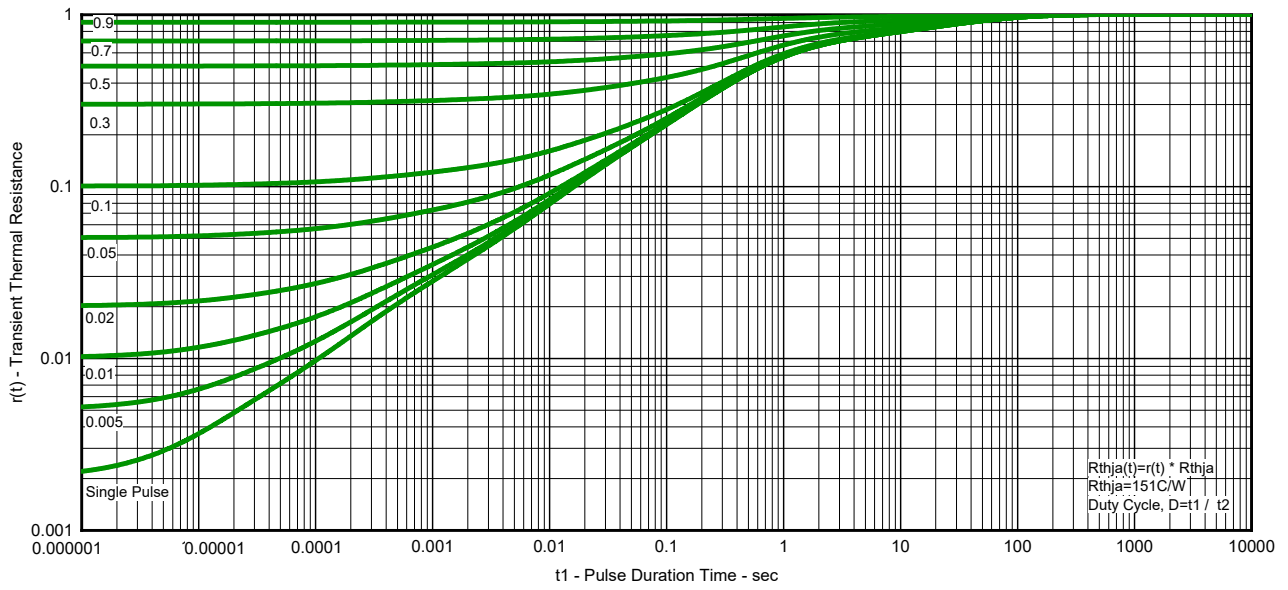
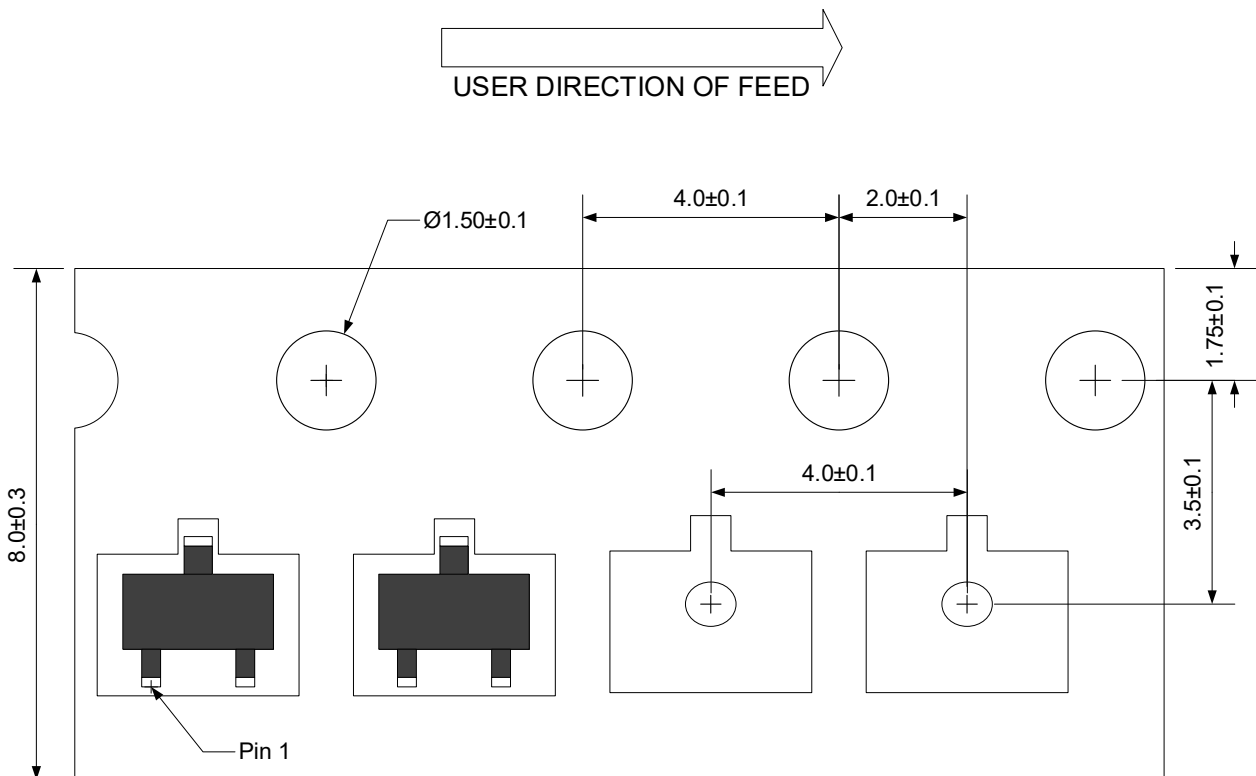


Fig.12 Transient Thermal Resistance

Ordering information

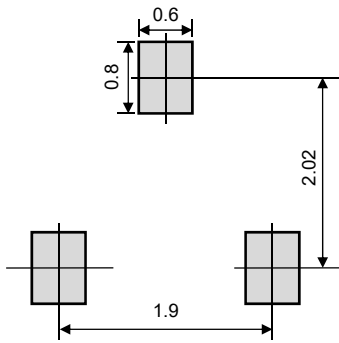
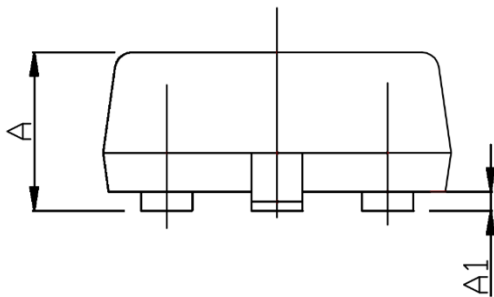
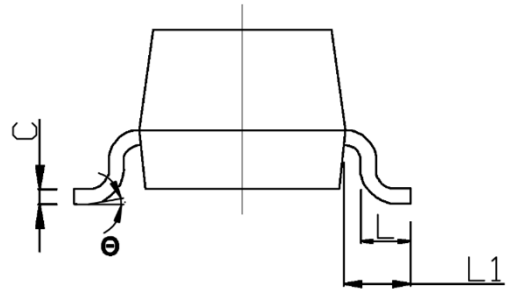
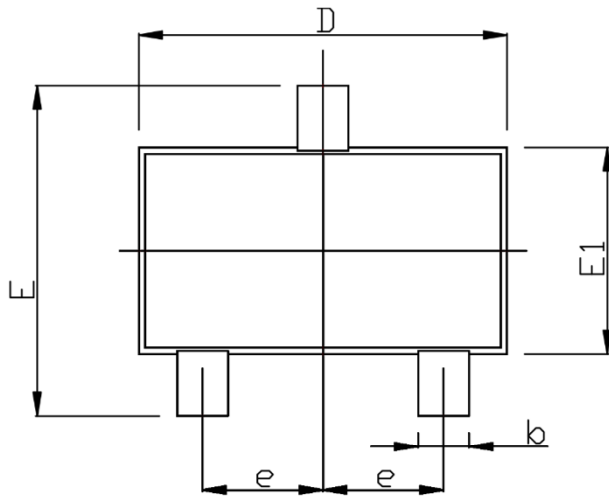
| Device    | Package          | Reel | Shipping           |
|-----------|------------------|------|--------------------|
| PPMT20V4A | SOT-23 (Pb-Free) | 7"   | 3000 / Tape & Reel |

Load with information



Unit:mm

Product dimension (SOT-23)




Suggested PCB Layout

Unit:mm

| Dim      | Millimeters |      | Inches    |       |
|----------|-------------|------|-----------|-------|
|          | Min         | Max  | Min       | Max   |
| A        | -           | 1.35 | -         | 0.053 |
| A1       | 0.04        | 0.15 | 0.002     | 0.006 |
| b        | 0.30        | 0.50 | 0.012     | 0.020 |
| c        | 0.08        | 0.21 | 0.003     | 0.008 |
| D        | 2.72        | 3.12 | 0.107     | 0.123 |
| E        | 2.10        | 2.64 | 0.083     | 0.104 |
| E1       | 1.10        | 1.50 | 0.043     | 0.059 |
| e        | 0.95 BSC    |      | 0.037 BSC |       |
| L        | 0.20        | 0.48 | 0.008     | 0.019 |
| L1       | 0.50        | 0.60 | 0.020     | 0.024 |
| $\theta$ | 0°          | 8°   | 0°        | 8°    |


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